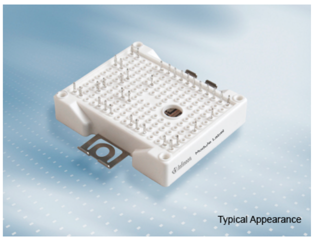
EasyPACK™ module with Trench/Fieldstop IGBT H3 and rapid diode and PressFIT / NTC



Features

- Electrical features
  - V_{CES} = 650 V
  - $I_{C\,nom}$ = 150 A / I_{CRM} = 300 A
  - Increased blocking voltage capability up to 650 V
  - Low inductive design
  - Low switching losses
  - Low $V_{CE,sat}$
- Mechanical features
  - Al_2O_3 substrate with low thermal resistance
  - Compact design
  - PressFIT contact technology
  - Rugged mounting due to integrated mounting clamps

Potential applications

- Three-level applications
- Motor drives
- Solar applications
- UPS systems

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

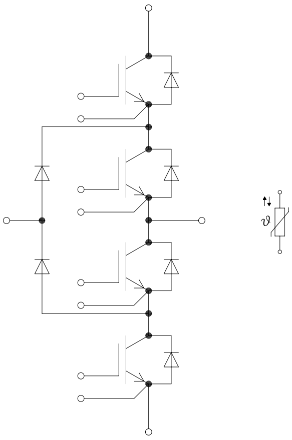


Table of contents

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, t = 1 min	3.0	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	11.5	mm
Creepage distance	d_{Creep}	terminal to terminal	6.3	mm
Clearance	d_{Clear}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to terminal	5.0	mm
Comparative tracking index	CTI		>200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			15		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_H=25°C, per switch		2.8		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	F		40		80	N
Weight	G			39		g

Note: The current under continuous operation is limited to 25A rms per connector pin

2 IGBT, T1 / T4

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	650	V
Implemented collector current	I_{CN}			150	A
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_H = 65 °C	85	A
Repetitive peak collector current	I_{CRM}	t_P = 1 ms		300	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values Min.	Typ.	Max.	Unit
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 150 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.68	2.00	V
			T_{vj} = 125 °C		1.86		
			T_{vj} = 150 °C		1.89		
Gate threshold voltage	V_{GEth}	I_C = 2.4 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.05	5.75	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CE} = 400 V			1.6		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 650 V, V_{GE} = 0 V			9.4		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 650 V, V_{GE} = 0 V			0.28		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 650 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.009	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 650 V, V_{GE} = 0 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Gon} = 7.5 Ω	T_{vj} = 25 °C		0.057		µs
			T_{vj} = 125 °C		0.059		
			T_{vj} = 150 °C		0.059		
Rise time (inductive load)	t_r	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Gon} = 7.5 Ω	T_{vj} = 25 °C		0.075		µs
			T_{vj} = 125 °C		0.076		
			T_{vj} = 150 °C		0.076		
Turn-off delay time (inductive load)	t_{doff}	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Goff} = 7.5 Ω	T_{vj} = 25 °C		0.329		µs
			T_{vj} = 125 °C		0.359		
			T_{vj} = 150 °C		0.362		
Fall time (inductive load)	t_f	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Goff} = 7.5 Ω	T_{vj} = 25 °C		0.024		µs
			T_{vj} = 125 °C		0.061		
			T_{vj} = 150 °C		0.077		
Turn-on energy loss per pulse	E_{on}	I_C = 150 A, V_{CE} = 300 V, $L_σ$ = 35 nH, V_{GE} = ±15 V, R_{Gon} = 7.5 Ω, di/dt = 1800 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		5.77		mJ
			T_{vj} = 125 °C		6.97		
			T_{vj} = 150 °C		7.21		
Turn-off energy loss per pulse	E_{off}	I_C = 150 A, V_{CE} = 300 V, $L_σ$ = 35 nH, V_{GE} = ±15 V, R_{Goff} = 7.5 Ω, dv/dt = 3600 V/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		2.53		mJ
			T_{vj} = 125 °C		3.46		
			T_{vj} = 150 °C		3.79		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT			0.771		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

3 IGBT, T2 / T3

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	650	V
Implemented collector current	I_{CN}			150	A
Continuous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_H = 65 °C	85	A
Repetitive peak collector current	I_{CRM}	t_P = 1 ms		300	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 150 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.45	1.90	V
			T_{vj} = 125 °C		1.61		
			T_{vj} = 150 °C		1.68		
Gate threshold voltage	V_{GEth}	I_C = 2.4 mA, V_{CE} = 20 V, T_{vj} = 25 °C		5.05	5.75	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CE} = 400 V			1.6		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 650 V, V_{GE} = 0 V			9.2		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 650 V, V_{GE} = 0 V			0.29		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 650 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.009	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 650 V, V_{GE} = 0 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Gon} = 1.5 Ω	T_{vj} = 25 °C		0.015		µs
			T_{vj} = 125 °C		0.017		
			T_{vj} = 150 °C		0.017		
Rise time (inductive load)	t_r	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Gon} = 1.5 Ω	T_{vj} = 25 °C		0.022		µs
			T_{vj} = 125 °C		0.028		
			T_{vj} = 150 °C		0.029		
Turn-off delay time (inductive load)	t_{doff}	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Goff} = 1.5 Ω	T_{vj} = 25 °C		0.186		µs
			T_{vj} = 125 °C		0.211		
			T_{vj} = 150 °C		0.216		
Fall time (inductive load)	t_f	I_C = 150 A, V_{CE} = 300 V, V_{GE} = ±15 V, R_{Goff} = 1.5 Ω	T_{vj} = 25 °C		0.094		µs
			T_{vj} = 125 °C		0.133		
			T_{vj} = 150 °C		0.147		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values Min.	Values Typ.	Values Max.	Unit
Turn-on energy loss per pulse	E_{on}	I_C = 150 A, V_{CE} = 300 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Gon} = 1.5 Ω, di/dt = 4500 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.341		mJ
			T_{vj} = 125 °C		0.629		
			T_{vj} = 150 °C		0.719		
Turn-off energy loss per pulse	E_{off}	I_C = 150 A, V_{CE} = 300 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Goff} = 1.5 Ω, dv/dt = 3900 V/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		3.5		mJ
			T_{vj} = 125 °C		4.66		
			T_{vj} = 150 °C		4.98		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT			0.771		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

4 Diode, D1 / D4

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	650	V
Continuous DC forward current	I_F			100	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		200	A
I^2t - value	I^2t	V_R = 0 V, t_P = 10 ms	T_{vj} = 125 °C	1750	A^2s
			T_{vj} = 150 °C	1650	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values Min.	Values Typ.	Values Max.	Unit
Forward voltage	V_F	I_F = 100 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.55	1.95	V
			T_{vj} = 125 °C		1.50		
			T_{vj} = 150 °C		1.45		
Peak reverse recovery current	I_{RM}	I_F = 100 A, V_R = 300 V, V_{GE} = -15 V, -di_F/dt = 4400 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		92.4		A
			T_{vj} = 125 °C		102		
			T_{vj} = 150 °C		106		

(table continues...)

Table 8 **(continued) Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	I_F = 100 A, V_R = 300 V, V_{GE} = -15 V, -di$_F$/dt = 4400 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		3.93		µC
			T_{vj} = 125 °C		7.53		
			T_{vj} = 150 °C		8.78		
Reverse recovery energy	E_{rec}	I_F = 100 A, V_R = 300 V, V_{GE} = -15 V, -di$_F$/dt = 4400 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.859		mJ
			T_{vj} = 125 °C		1.65		
			T_{vj} = 150 °C		1.94		
Thermal resistance, junction to heat sink	R_{thJH}	per diode			0.975		K/W
Temperature under switching conditions	$T_{vj\ op}$			-40		150	°C

5 Diode, D2 / D3

Table 9 **Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	650	V
Continuous DC forward current	I_F			100	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		200	A
I^2t - value	I^2t	V_R = 0 V, t_P = 10 ms	T_{vj} = 125 °C	1750	A^2s
			T_{vj} = 150 °C	1650	

Table 10 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 100 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.55	1.95	V
			T_{vj} = 125 °C		1.50		
			T_{vj} = 150 °C		1.45		
Peak reverse recovery current	I_{RM}	I_F = 100 A, V_R = 300 V, V_{GE} = -15 V, -di$_F$/dt = 4400 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		92.4		A
			T_{vj} = 125 °C		102		
			T_{vj} = 150 °C		106		

(table continues...)

Table 10 **(continued) Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	I_F = 100 A, V_R = 300 V, V_{GE} = -15 V, -di$_F$/dt = 4400 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		3.93		µC
			T_{vj} = 125 °C		7.53		
			T_{vj} = 150 °C		8.78		
Reverse recovery energy	E_{rec}	I_F = 100 A, V_R = 300 V, V_{GE} = -15 V, -di$_F$/dt = 4400 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.859		mJ
			T_{vj} = 125 °C		1.65		
			T_{vj} = 150 °C		1.94		
Thermal resistance, junction to heat sink	R_{thJH}	per diode			0.975		K/W
Temperature under switching conditions	$T_{vj\ op}$			-40		150	°C

6 Diode, D5 / D6

Table 11 **Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	650	V
Continuous DC forward current	I_F			150	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		300	A
I^2t - value	I^2t	V_R = 0 V, t_P = 10 ms	T_{vj} = 125 °C	2120	A^2s
			T_{vj} = 150 °C	1810	

Table 12 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 150 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.50	2.05	V
			T_{vj} = 125 °C		1.48		
			T_{vj} = 150 °C		1.47		
Peak reverse recovery current	I_{RM}	I_F = 150 A, V_R = 300 V, V_{GE} = -15 V, -di$_F$/dt = 1800 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		41.8		A
			T_{vj} = 125 °C		69.7		
			T_{vj} = 150 °C		75.4		

(table continues...)

Table 12 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	I_F = 150 A, V_R = 300 V, V_{GE} = -15 V, -di_F/dt = 1800 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		4.93		µC
			T_{vj} = 125 °C		8.81		
			T_{vj} = 150 °C		9.27		
Reverse recovery energy	E_{rec}	I_F = 150 A, V_R = 300 V, V_{GE} = -15 V, -di_F/dt = 1800 A/µs (T_{vj} = 150 °C)	T_{vj} = 25 °C		0.426		mJ
			T_{vj} = 125 °C		1.02		
			T_{vj} = 150 °C		1.22		
Thermal resistance, junction to heat sink	R_{thJH}	per diode			0.888		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		150	°C

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\ K))]$		3433		K

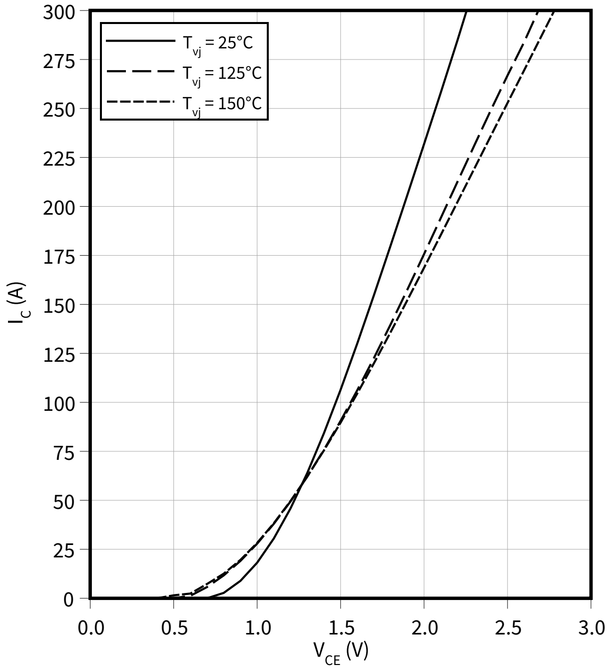
Note: Specification according to the valid application note.

8 Characteristics diagrams

Output characteristic (typical), IGBT, T1 / T4

$I_C = f(V_{CE})$

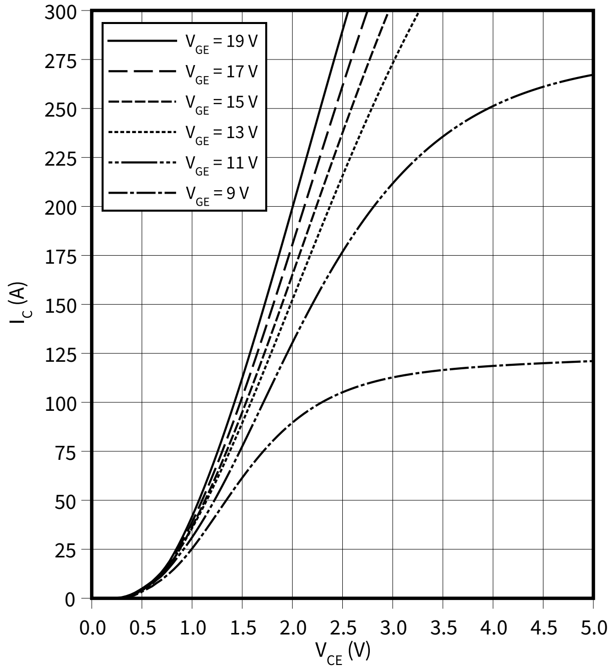
$V_{GE} = 15\ V$



Output characteristic field (typical), IGBT, T1 / T4

$I_C = f(V_{CE})$

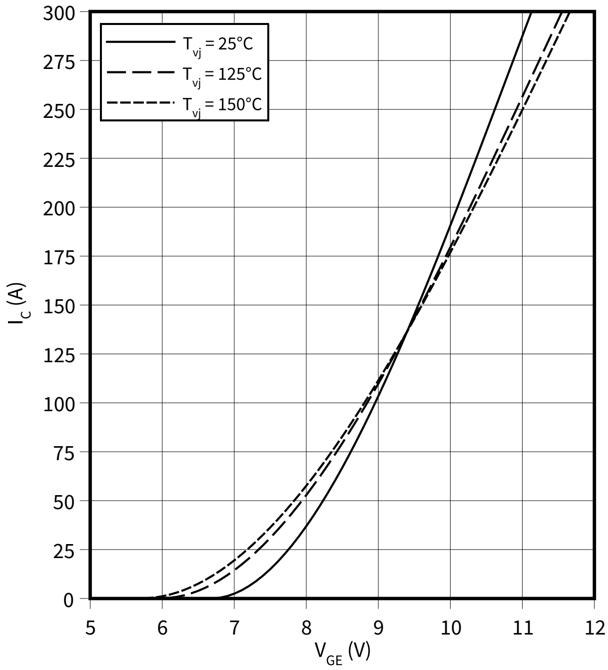
$T_{vj} = 150\ °C$



Transfer characteristic (typical), IGBT, T1 / T4

$I_C = f(V_{GE})$

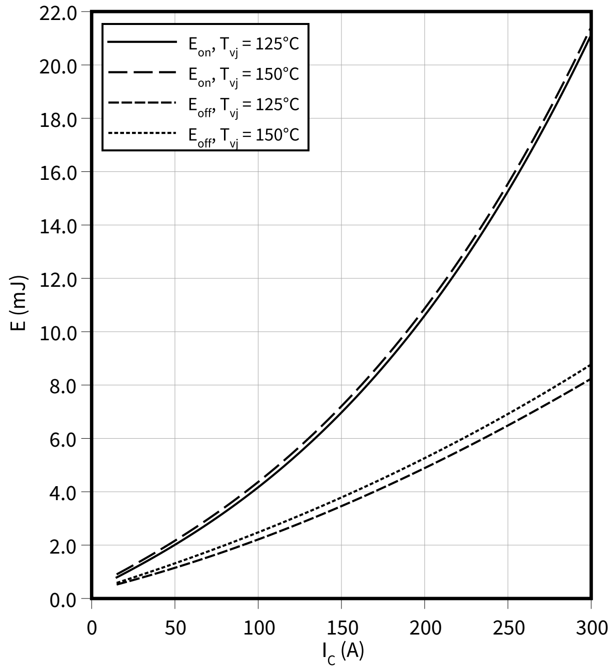
$V_{CE} = 20\ V$



Switching losses (typical), IGBT, T1 / T4

$E = f(I_C)$

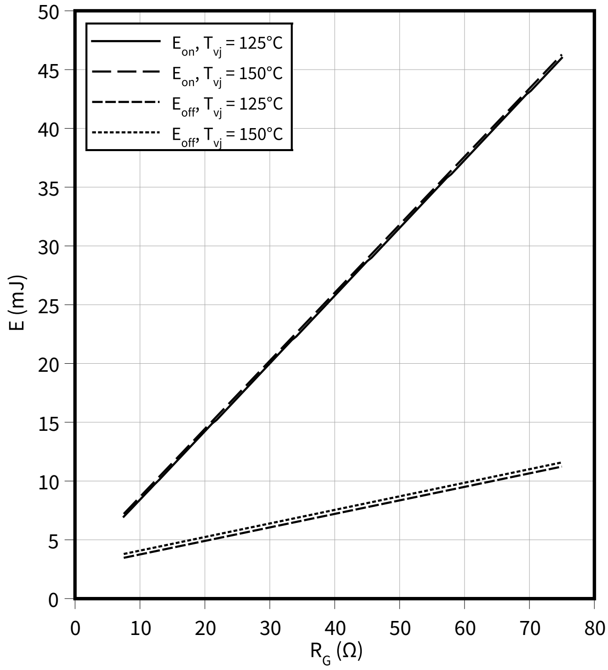
$R_{Goff} = 7.5\ \Omega$, $R_{Gon} = 7.5\ \Omega$, $V_{CE} = 300\ V$, $V_{GE} = \pm\ 15\ V$



Switching losses (typical), IGBT, T1 / T4

$E = f(R_G)$

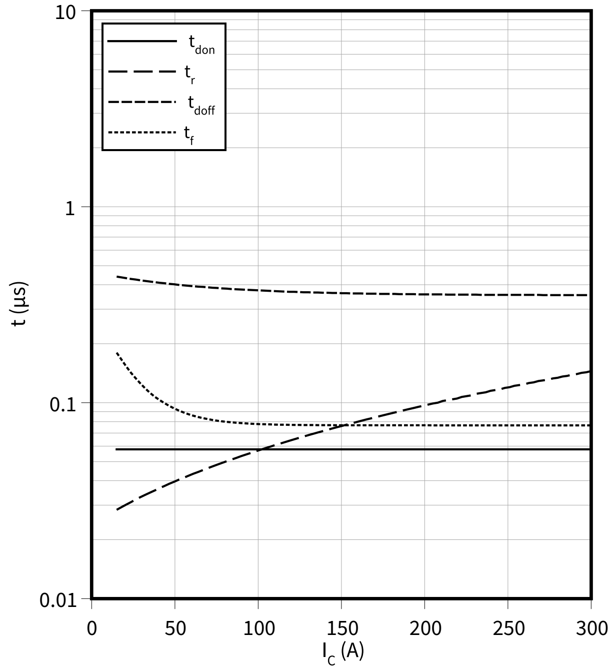
$I_C = 150$ A, $V_{CE} = 300$ V, $V_{GE} = \pm 15$ V



Switching times (typical), IGBT, T1 / T4

$t = f(I_C)$

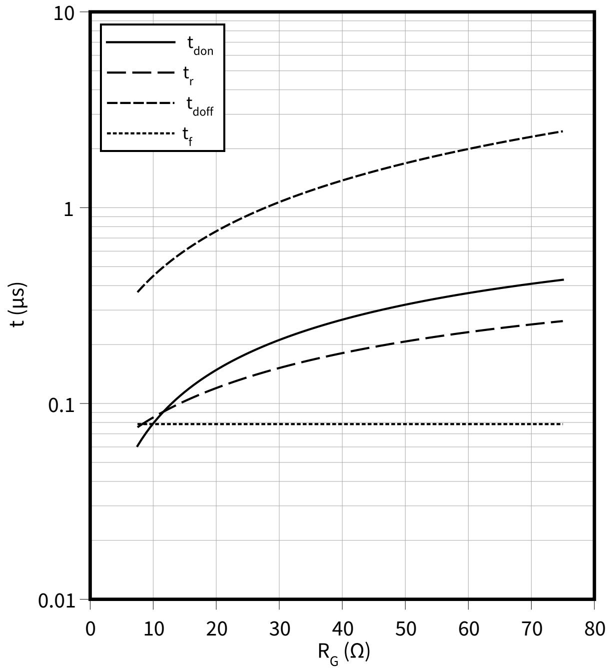
$R_{Goff} = 7.5\ \Omega$, $R_{Gon} = 7.5\ \Omega$, $V_{CE} = 300$ V, $V_{GE} = \pm 15$ V, $T_{vj} = 150$ °C



Switching times (typical), IGBT, T1 / T4

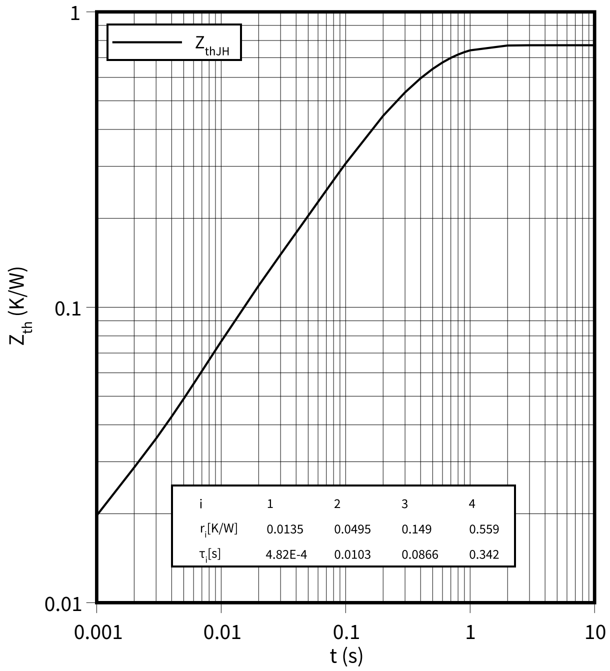
$t = f(R_G)$

$I_C = 150$ A, $V_{CE} = 300$ V, $V_{GE} = \pm 15$ V, $T_{vj} = 150$ °C



Transient thermal impedance , IGBT, T1 / T4

$Z_{th} = f(t)$

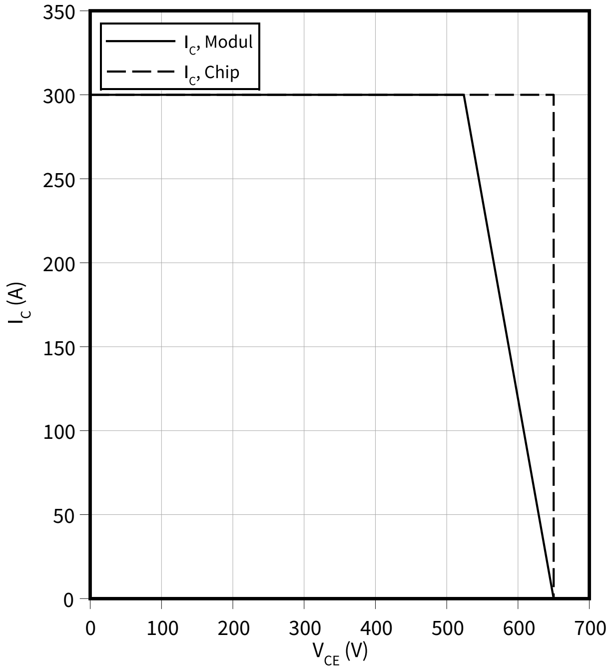


i	1	2	3	4
r_i[K/W]	0.0135	0.0495	0.149	0.559
τ_i[s]	4.82E-4	0.0103	0.0866	0.342

Reverse bias safe operating area (RBSOA), IGBT, T1 / T4

$I_C = f(V_{CE})$

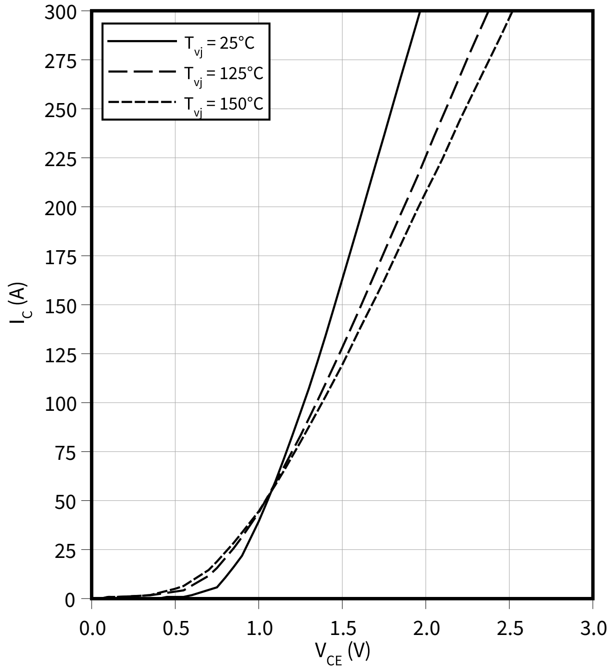
$R_{Goff} = 7.5\ \Omega$, $V_{GE} = \pm 15\ V$, $T_{vj} = 150\ °C$



Output characteristic (typical), IGBT, T2 / T3

$I_C = f(V_{CE})$

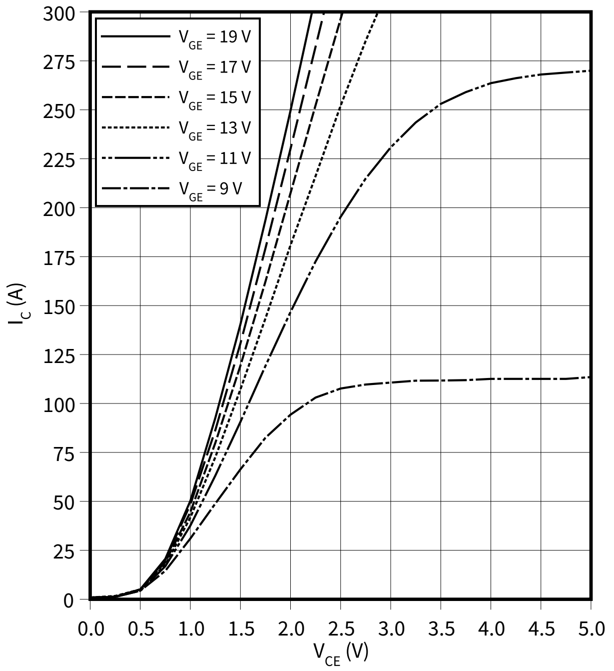
$V_{GE} = 15\ V$



Output characteristic field (typical), IGBT, T2 / T3

$I_C = f(V_{CE})$

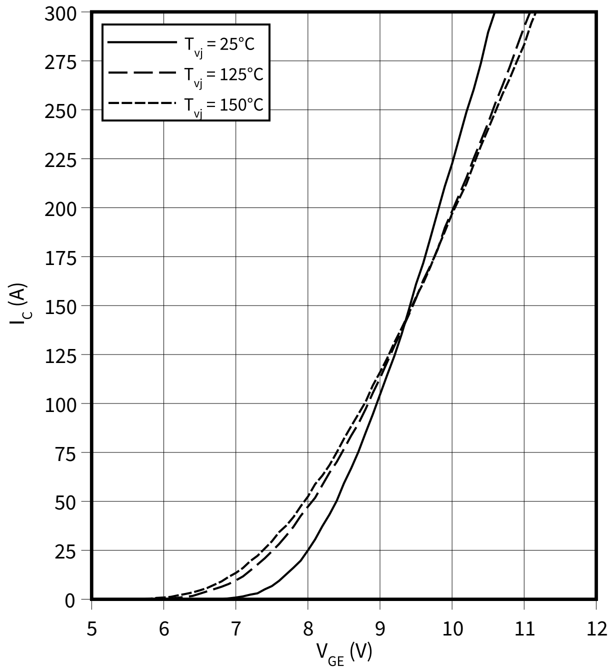
$T_{vj} = 150\ °C$



Transfer characteristic (typical), IGBT, T2 / T3

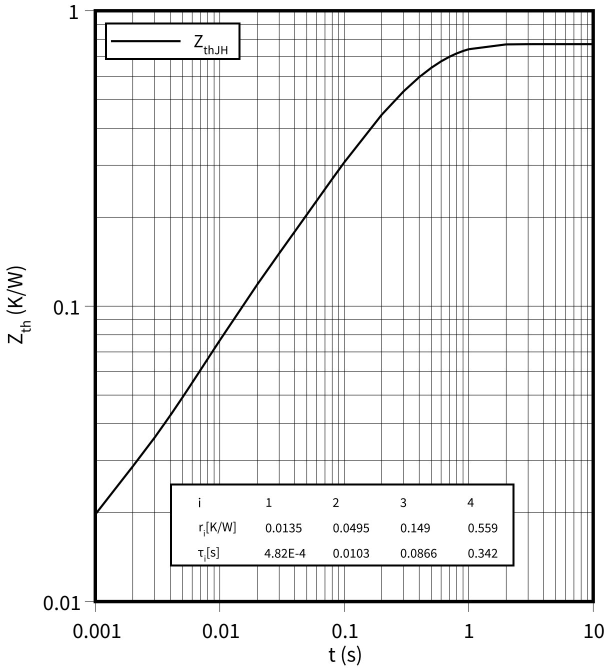
$I_C = f(V_{GE})$

$V_{CE} = 20\ V$



Transient thermal impedance , IGBT, T2 / T3

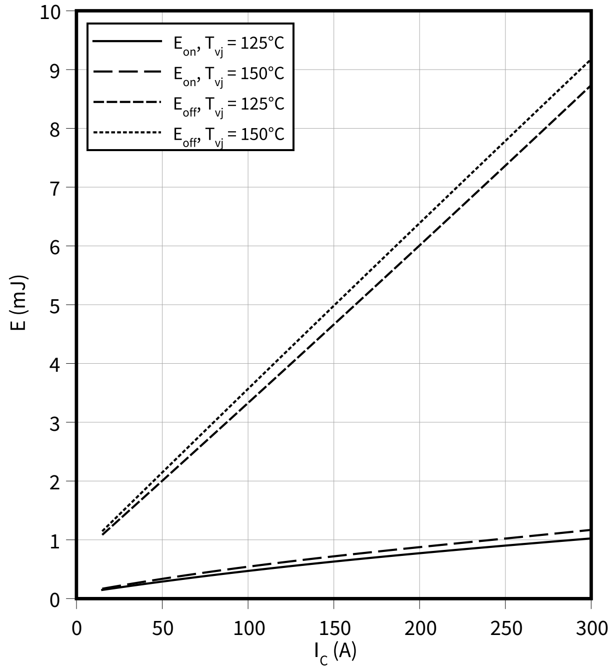
$Z_{th} = f(t)$



Switching losses (typical), IGBT, T2 / T3

$E = f(I_C)$

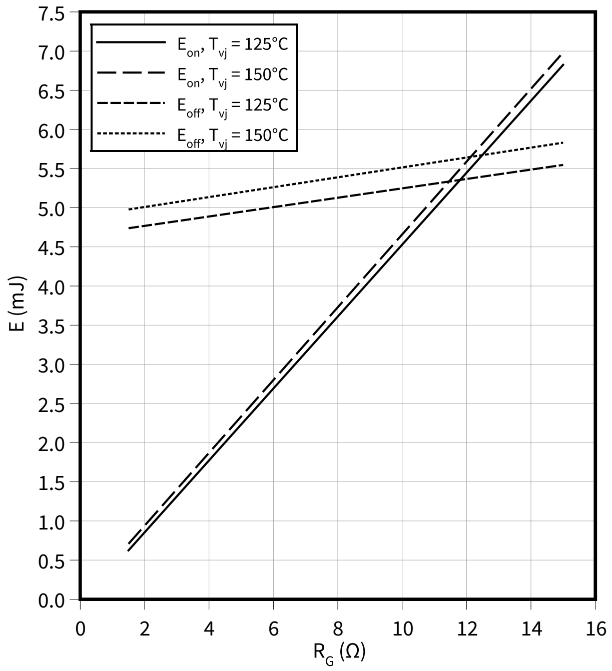
$R_{Goff} = 1.5\ \Omega$, $R_{Gon} = 1.5\ \Omega$, $V_{GE} = \pm15$ V, $V_{CE} = 300$ V



Switching losses (typical), IGBT, T2 / T3

$E = f(R_G)$

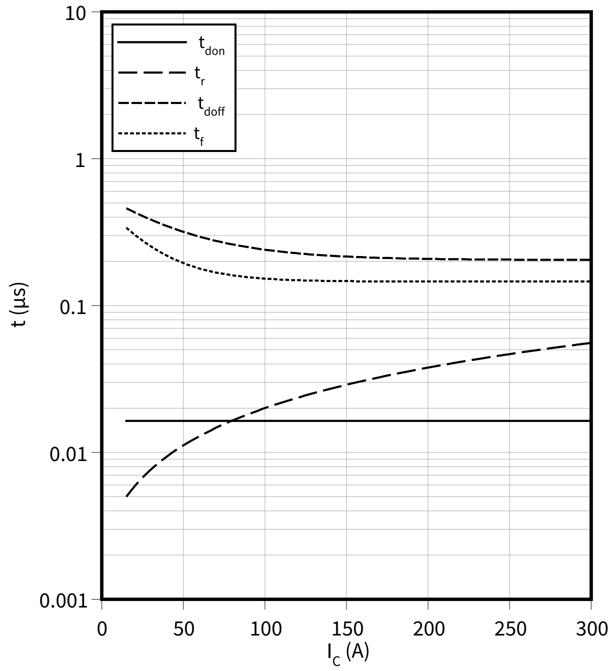
$V_{GE} = \pm15$ V, $I_C = 150$ A, $V_{CE} = 300$ V



Switching times (typical), IGBT, T2 / T3

$t = f(I_C)$

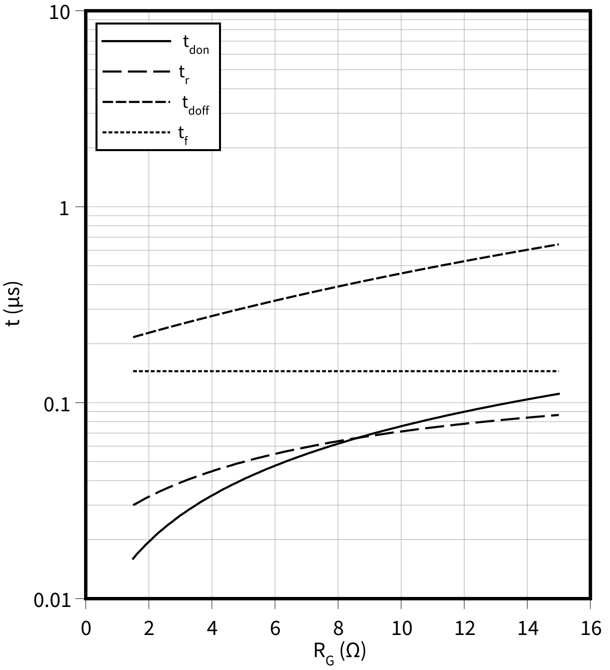
$R_{Goff} = 1.5\ \Omega$, $R_{Gon} = 1.5\ \Omega$, $V_{GE} = \pm15$ V, $V_{CE} = 300$ V, $T_{vj} = 150$ °C



Switching times (typical), IGBT, T2 / T3

$t = f(R_G)$

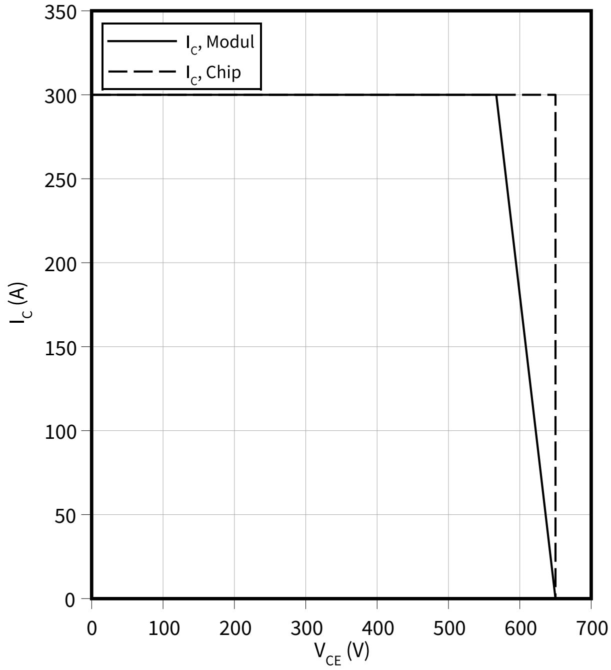
$V_{GE} = \pm 15\ V$, $I_C = 150\ A$, $V_{CE} = 300\ V$, $T_{vj} = 150\ °C$



Reverse bias safe operating area (RBSOA), IGBT, T2 / T3

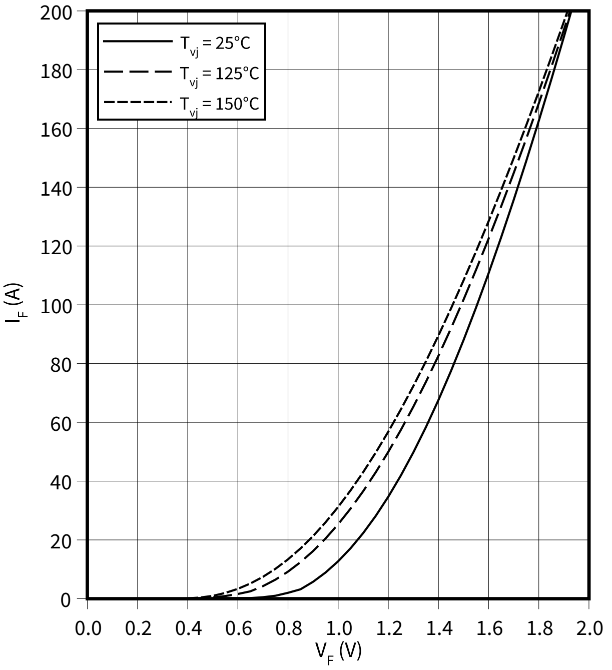
$I_C = f(V_{CE})$

$R_{Goff} = 1.5\ \Omega$, $V_{GE} = \pm 15\ V$, $T_{vj} = 150\ °C$



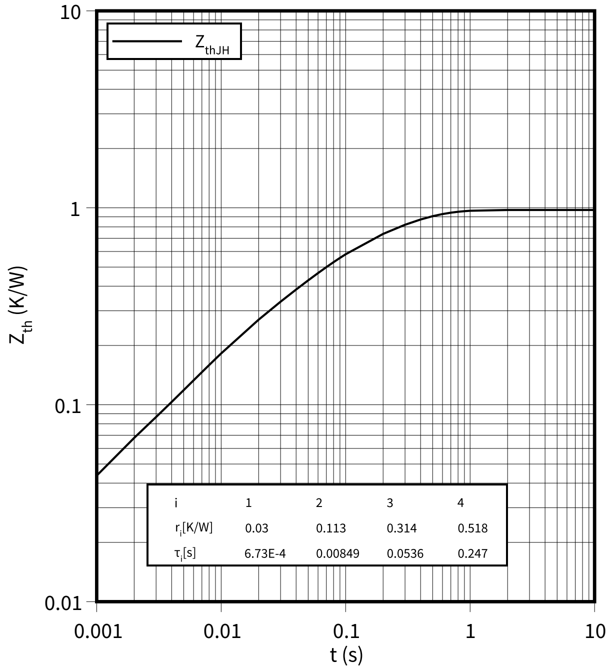
Forward characteristic (typical), Diode, D1 / D4

$I_F = f(V_F)$



Transient thermal impedance, Diode, D1 / D4

$Z_{th} = f(t)$

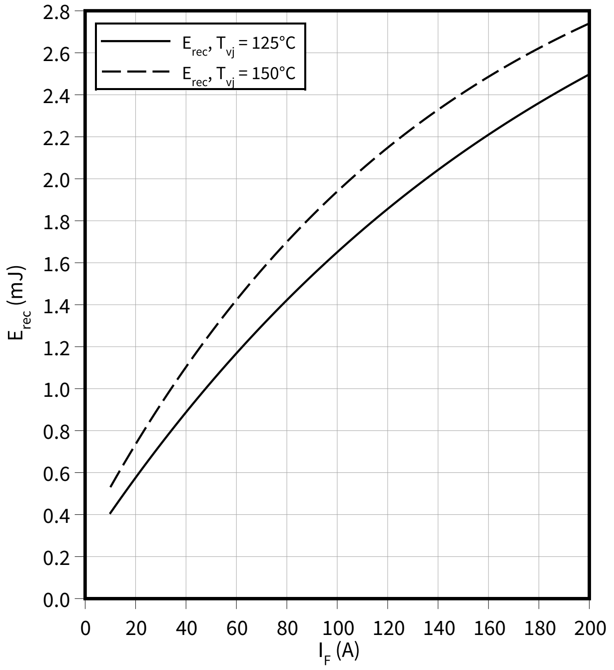


i	1	2	3	4
r_i[K/W]	0.03	0.113	0.314	0.518
τ_i[s]	6.73E-4	0.00849	0.0536	0.247

Switching losses (typical), Diode, D1 / D4

$E_{rec} = f(I_F)$

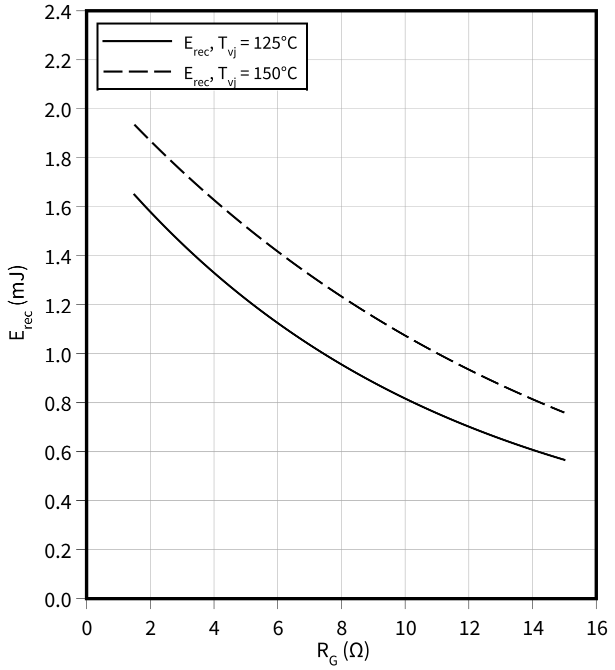
$R_{Gon} = 1.5\ \Omega$, $V_R = 300$ V



Switching losses (typical), Diode, D1 / D4

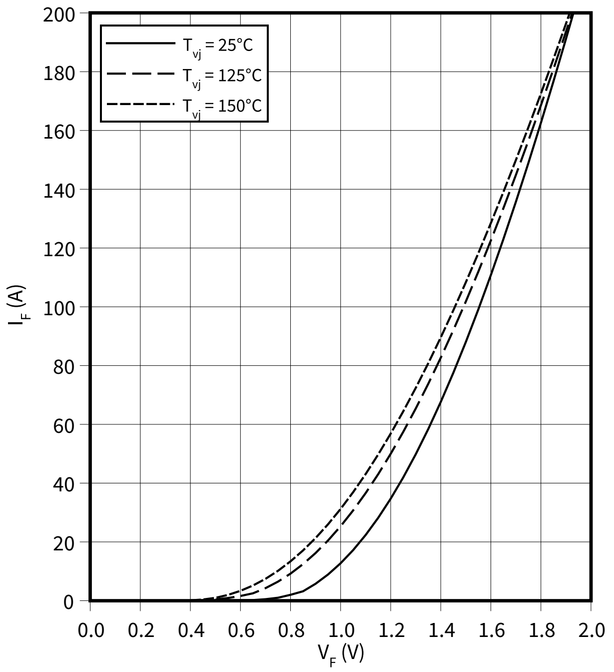
$E_{rec} = f(R_G)$

$I_F = 100$ A, $V_R = 300$ V



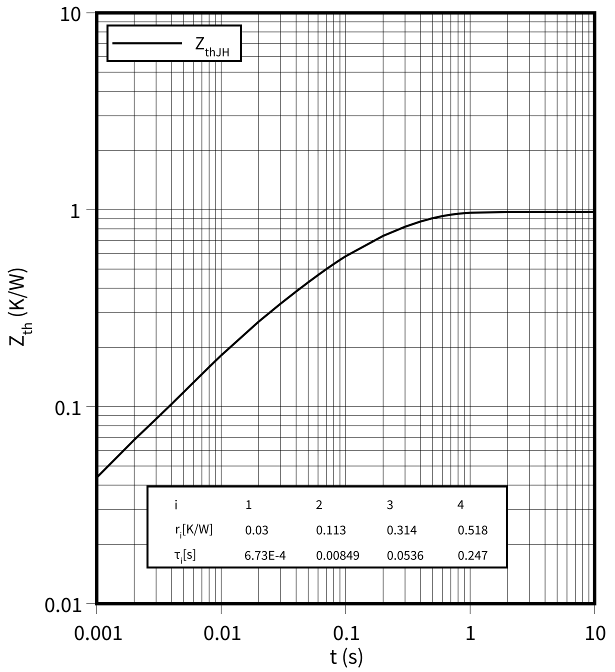
Forward characteristic (typical), Diode, D2 / D3

$I_F = f(V_F)$



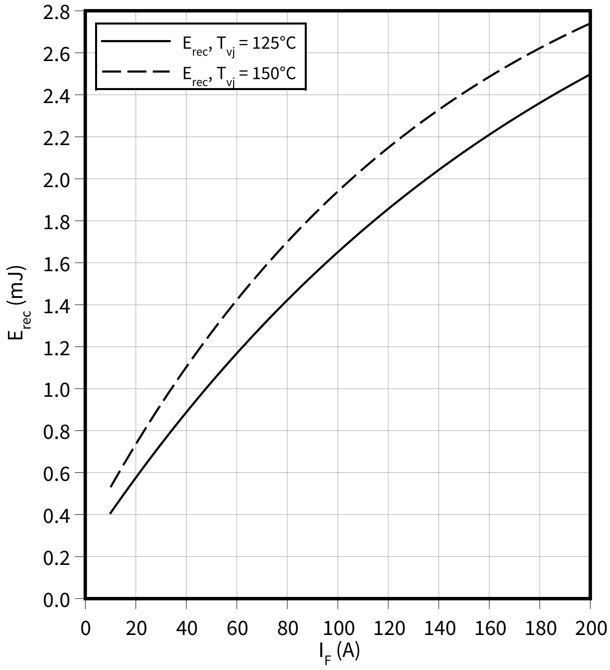
Transient thermal impedance, Diode, D2 / D3

$Z_{th} = f(t)$

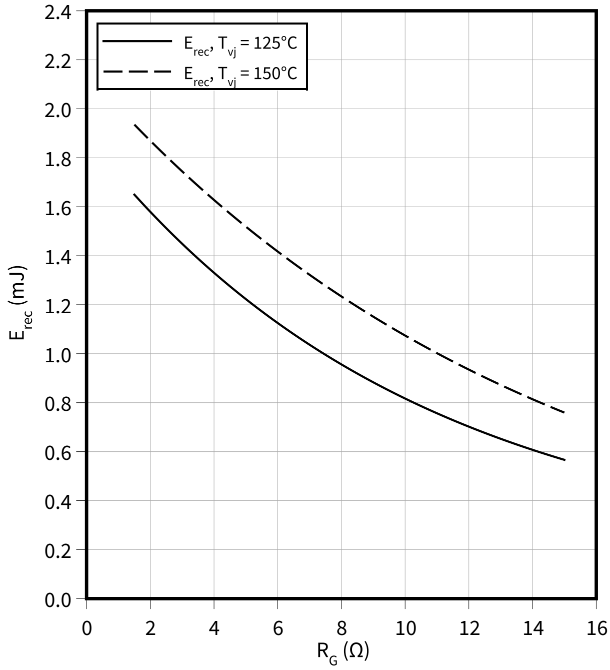


i	1	2	3	4
r_i[K/W]	0.03	0.113	0.314	0.518
τ_i[s]	6.73E-4	0.00849	0.0536	0.247

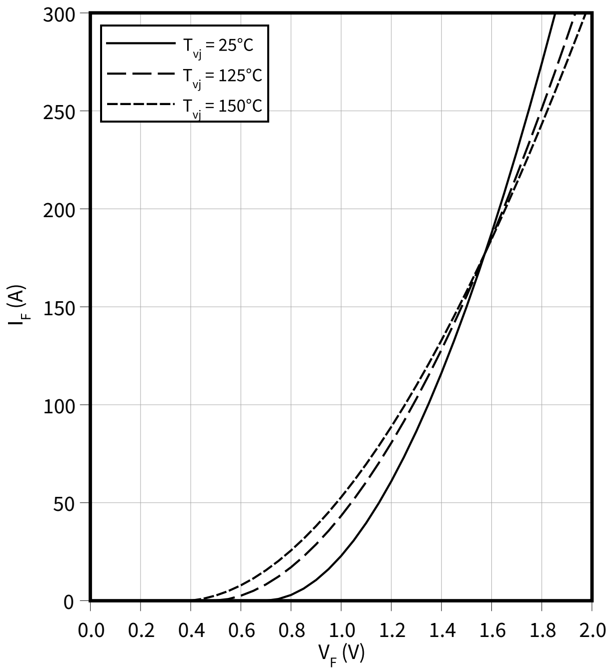
Switching losses (typical), Diode, D2 / D3
$E_{rec} = f(I_F)$
$R_{Gon} = 1.5\ \Omega$, $V_R = 300\ V$



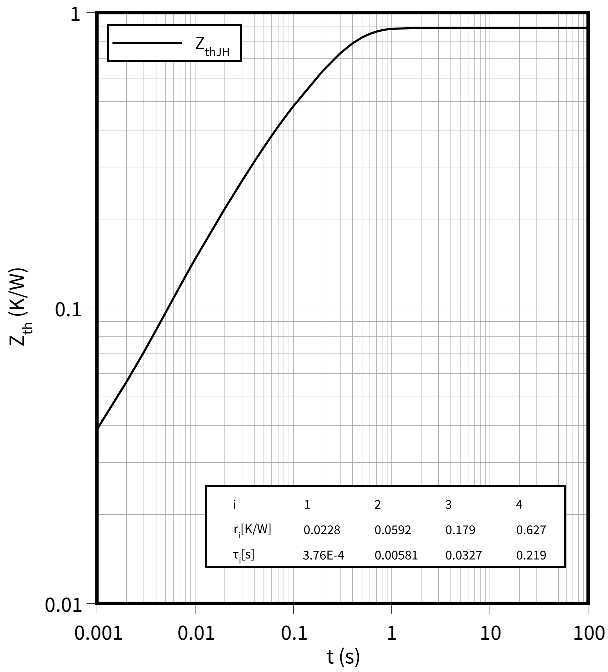
Switching losses (typical), Diode, D2 / D3
$E_{rec} = f(R_G)$
$I_F = 100\ A$, $V_R = 300\ V$



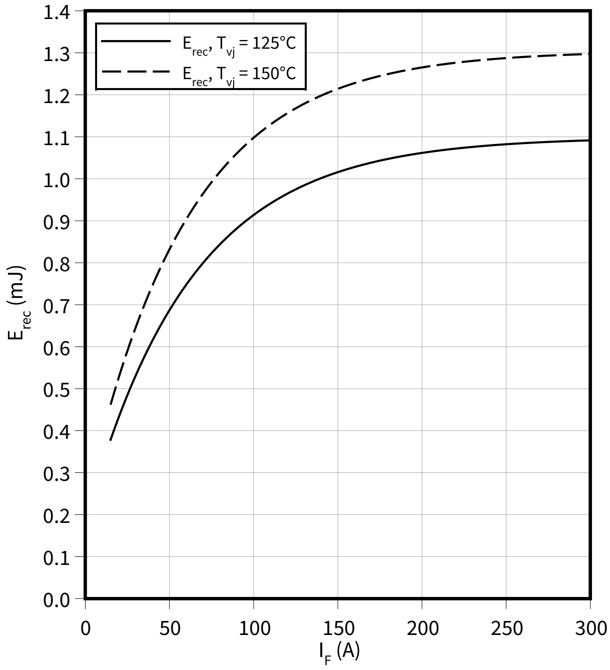
Forward characteristic (typical), Diode, D5 / D6
$I_F = f(V_F)$



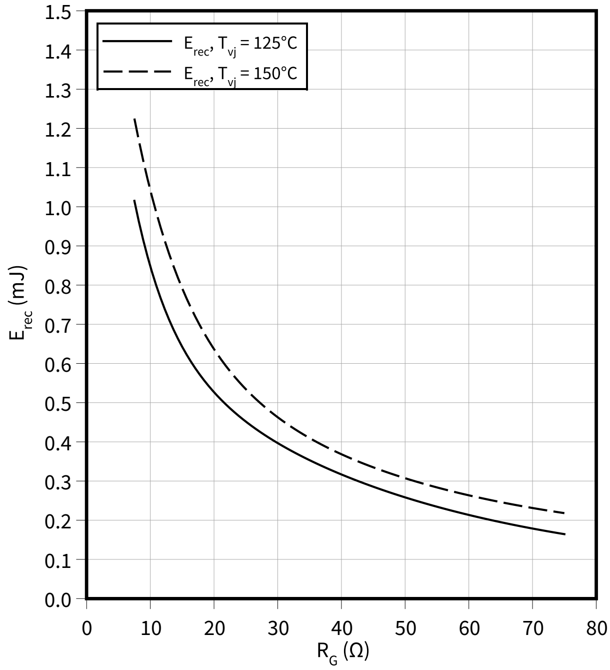
Transient thermal impedance, Diode, D5 / D6
$Z_{th} = f(t)$



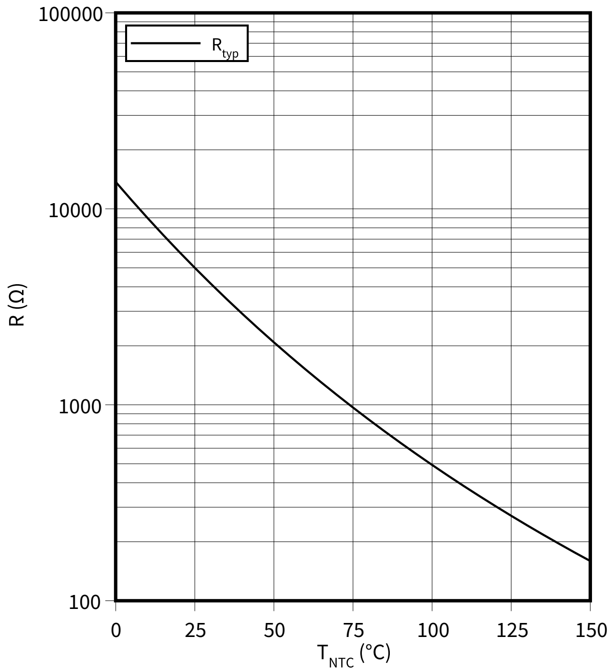
Switching losses (typical), Diode, D5 / D6
$E_{rec} = f(I_F)$
$R_{Gon} = 7.5\ \Omega$, $V_R = 300$ V



Switching losses (typical), Diode, D5 / D6
$E_{rec} = f(R_G)$
$I_F = 150$ A, $V_R = 300$ V



Temperature characteristic (typical), NTC-Thermistor
$R = f(T_{NTC})$



9 Circuit diagram

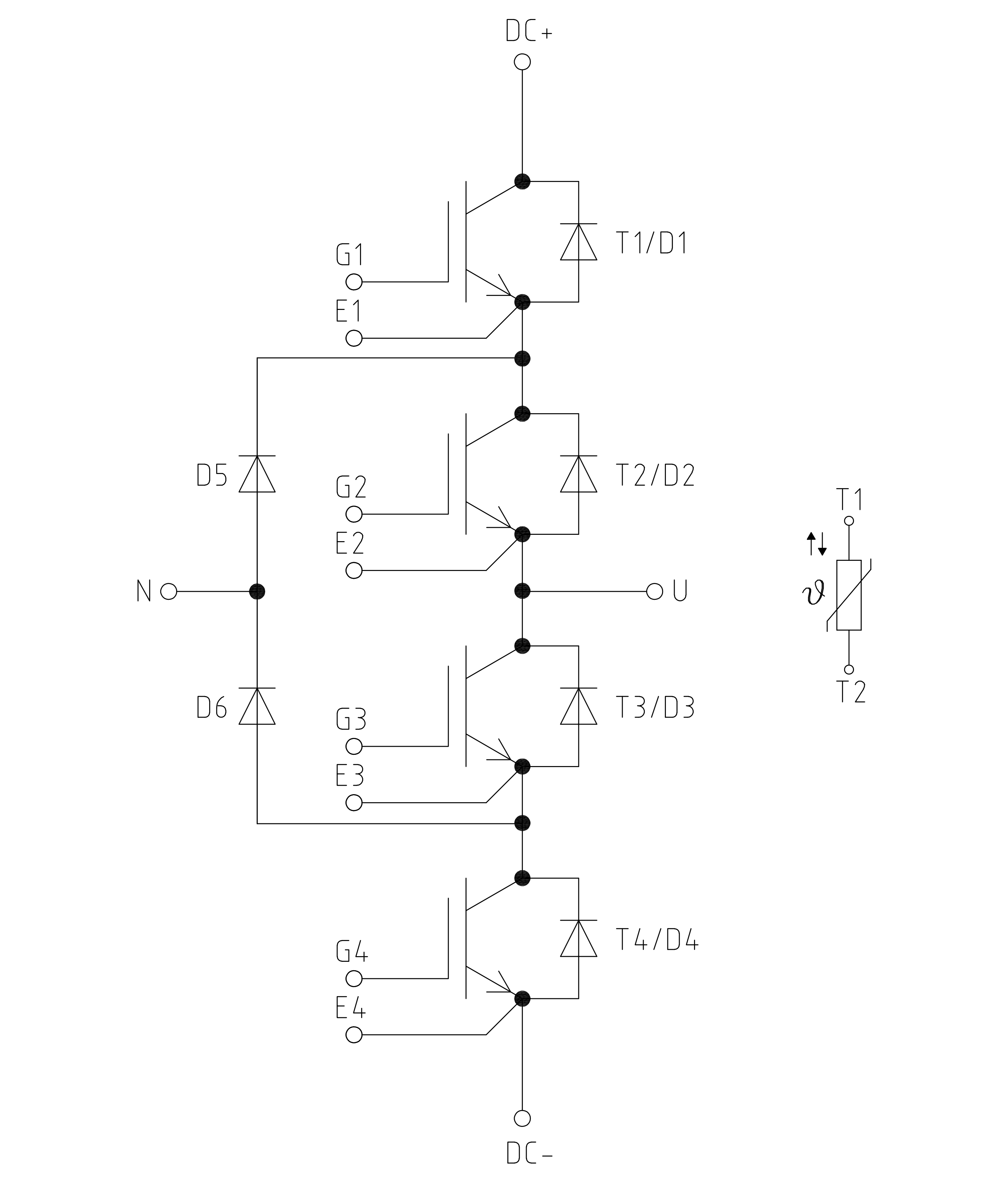


Figure 1

10 Package outlines

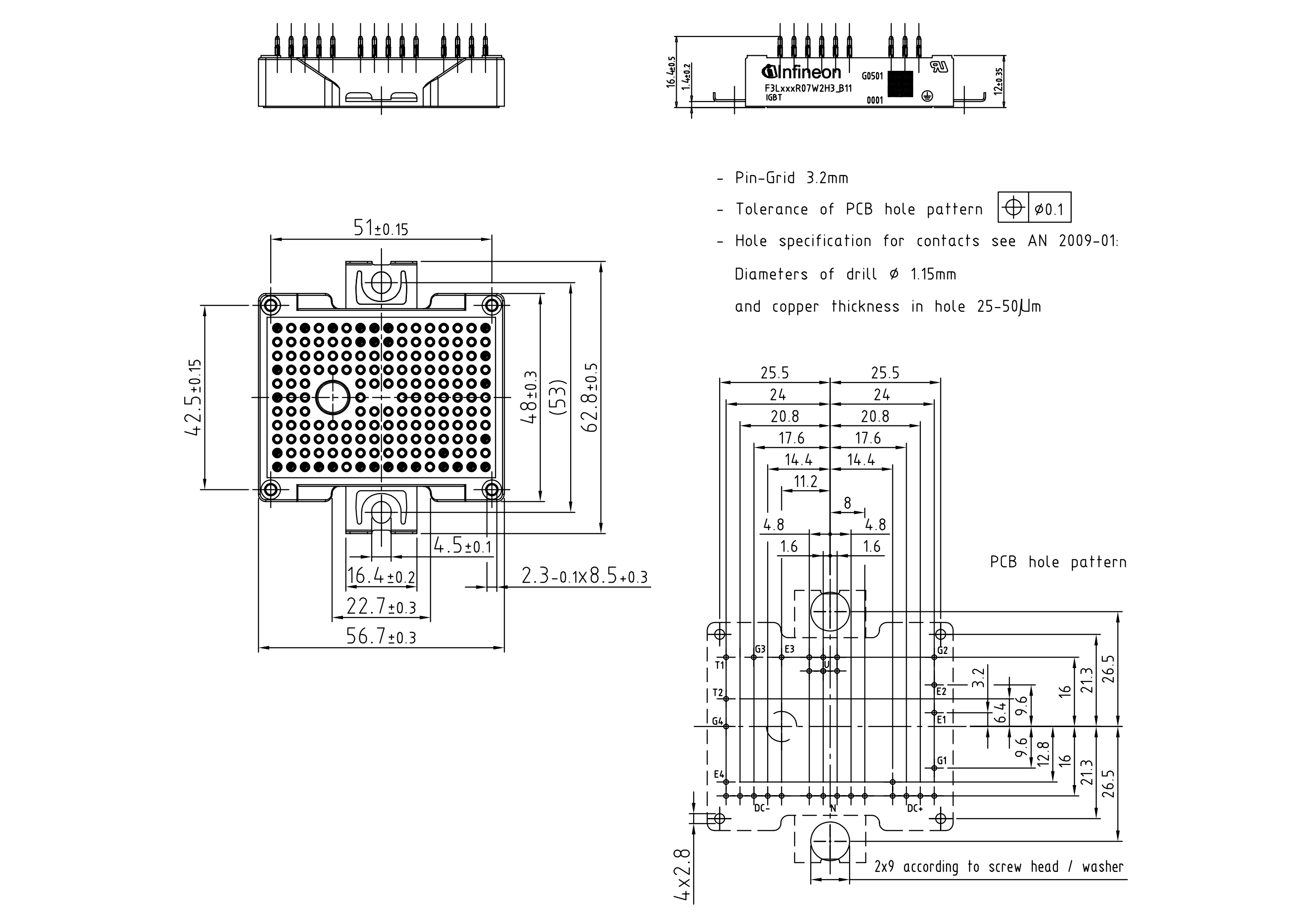


Figure 2

11 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2021-08-24	Initial version
1.00	2021-12-13	Final datasheet

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